



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ\text{C}$
60V	40m Ω @ $V_{GS} = 10V$	5.0A
	55m Ω @ $V_{GS} = 4.5V$	4.2A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

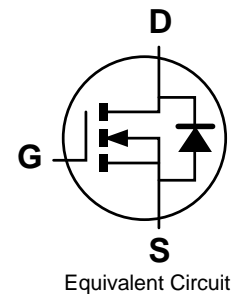
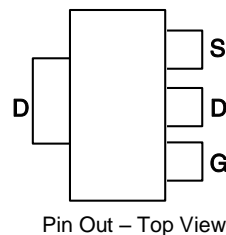
- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (Approximate)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.0 4.0	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	7.1 5.5	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	30	A
Maximum Body Diode Continuous Current			I _S	3.4	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	14.2	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	10	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.2	W
	T _A = +70°C		0.7	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	106	°C/W
	t < 10s		53	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2	W
	T _A = +70°C		1.2	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	65	°C/W
	t < 10s		34	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	9	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	30	40	mΩ	V _{GS} = 10V, I _D = 12A
		—	35	55		V _{GS} = 4.5V, I _D = 6A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	1,287	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	57	—		
Reverse Transfer Capacitance	C _{RSS}	—	44	—		
Gate Resistance	R _G	—	1.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _G	—	22.4	—	nC	V _{DS} = 30V, I _D = 4.3A
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	10.4	—		
Gate-Source Charge	Q _{GS}	—	4.9	—		
Gate-Drain Charge	Q _{GD}	—	3.0	—	ns	V _{GS} = 10V, V _{DD} = 30V, R _G = 6Ω, I _D = 4.3A
Turn-On Delay Time	t _{D(ON)}	—	6.6	—		
Turn-On Rise Time	t _R	—	8.1	—		
Turn-Off Delay Time	t _{D(OFF)}	—	20.1	—		
Turn-Off Fall Time	t _F	—	4.0	—	ns	I _S = 4.3A, di/dt = 100A/μs
Body Diode Reverse Recovery Time	t _{RR}	—	18	—		
Body Diode Reverse Recovery Charge	Q _{RR}	—	11.9	—	nC	I _S = 4.3A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

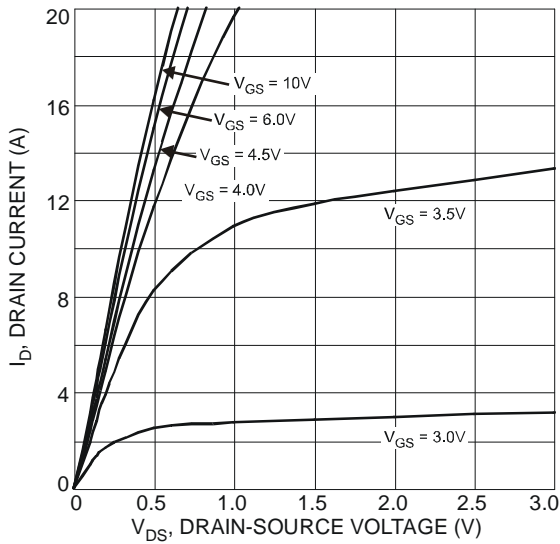


Figure 1 Typical Output Characteristic

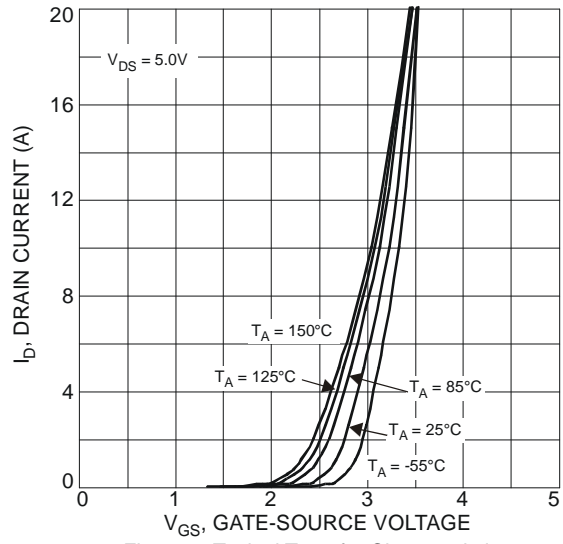


Figure 2 Typical Transfer Characteristics

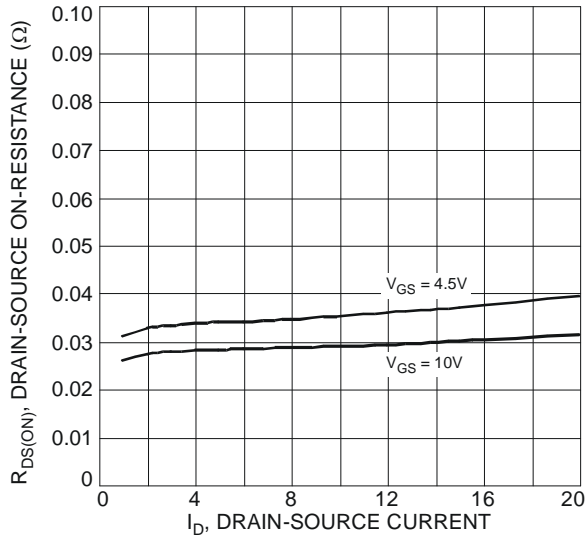


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

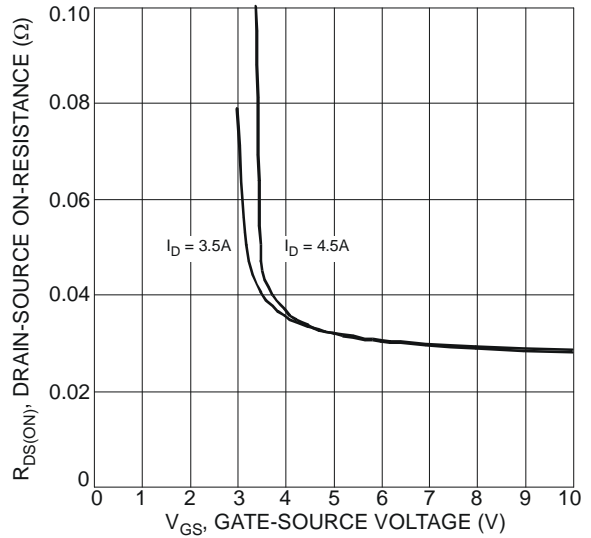


Figure 4 Typical On-Resistance vs. Drain Current and Gate Voltage

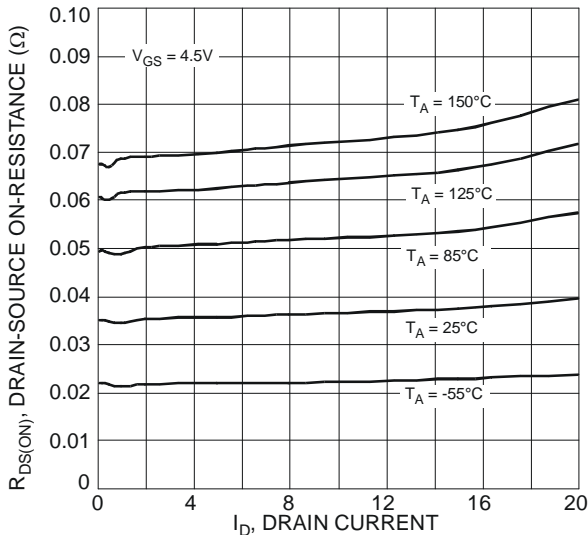


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

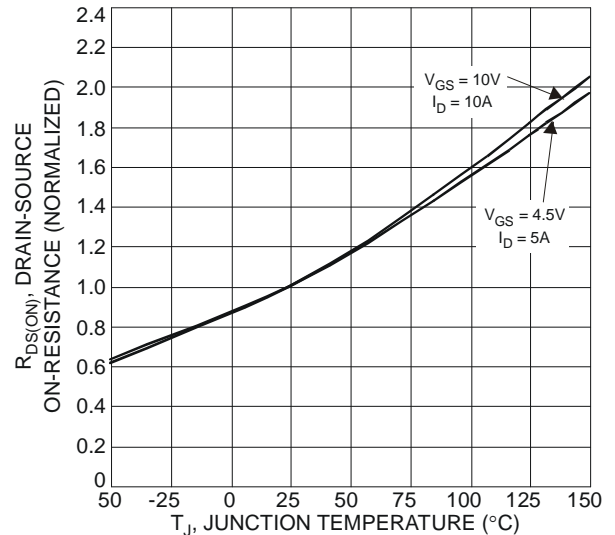


Figure 6 On-Resistance Variation with Temperature

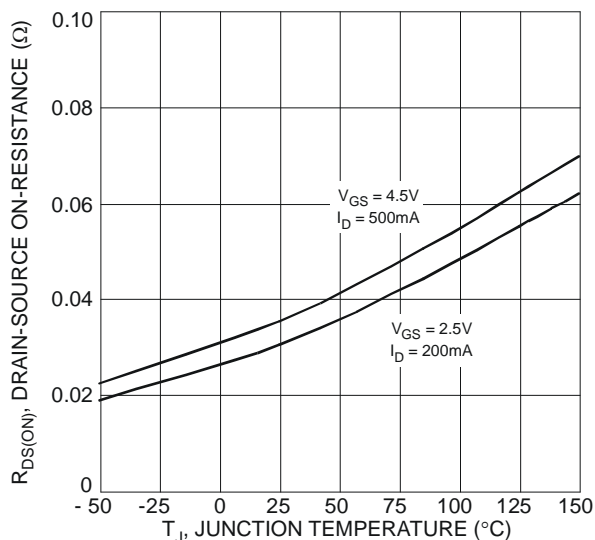


Figure 7 On-Resistance Variation with Temperature

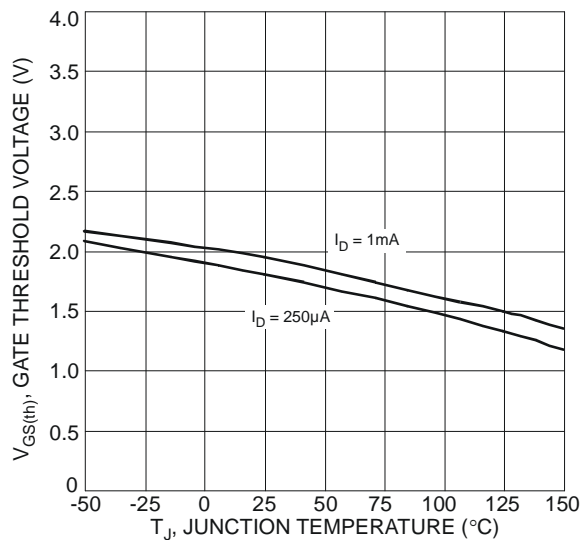


Figure 8 Gate Threshold Variation vs. Ambient Temperature

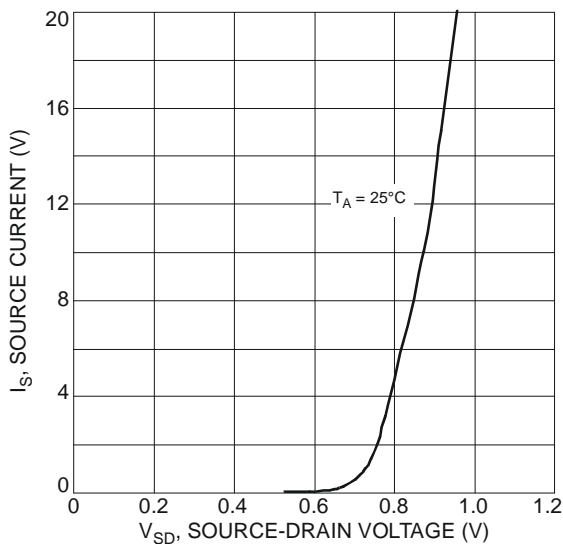


Figure 9 Diode Forward Voltage vs. Current

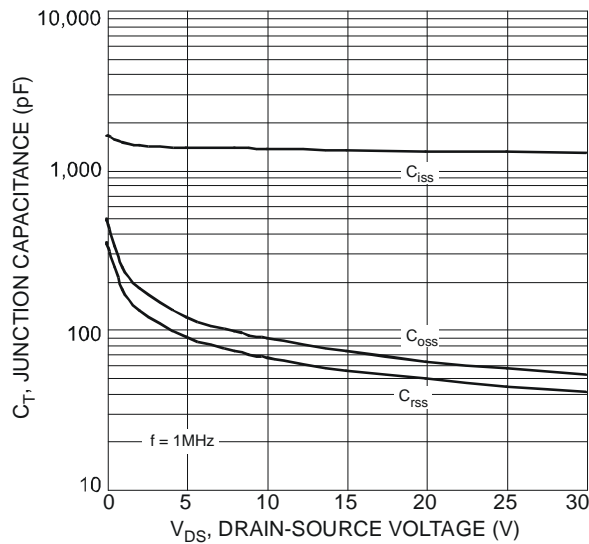


Figure 10 Typical Junction Capacitance

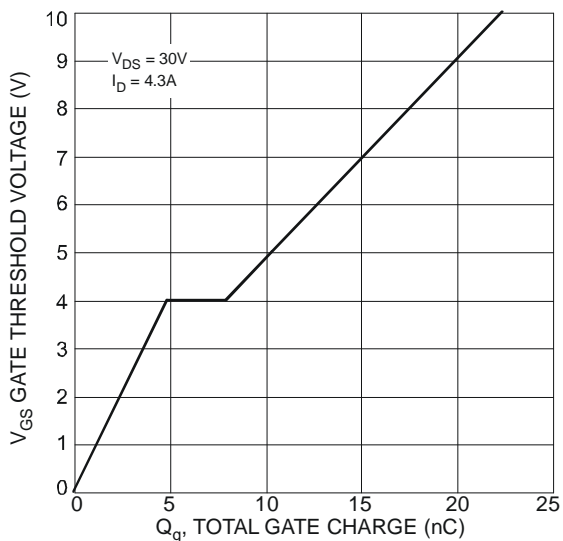


Figure 11 Gate Charge

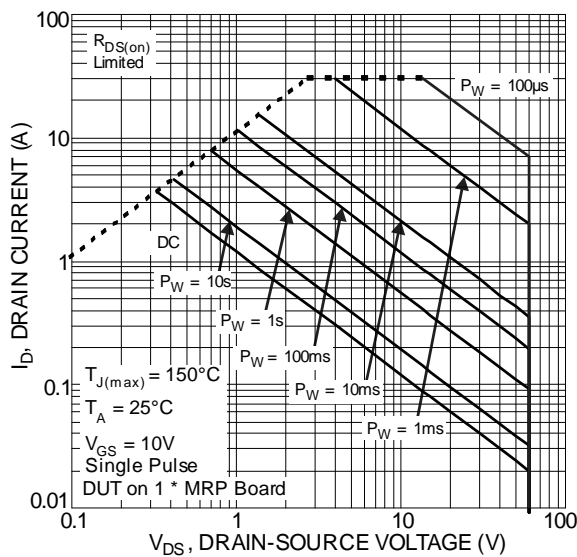
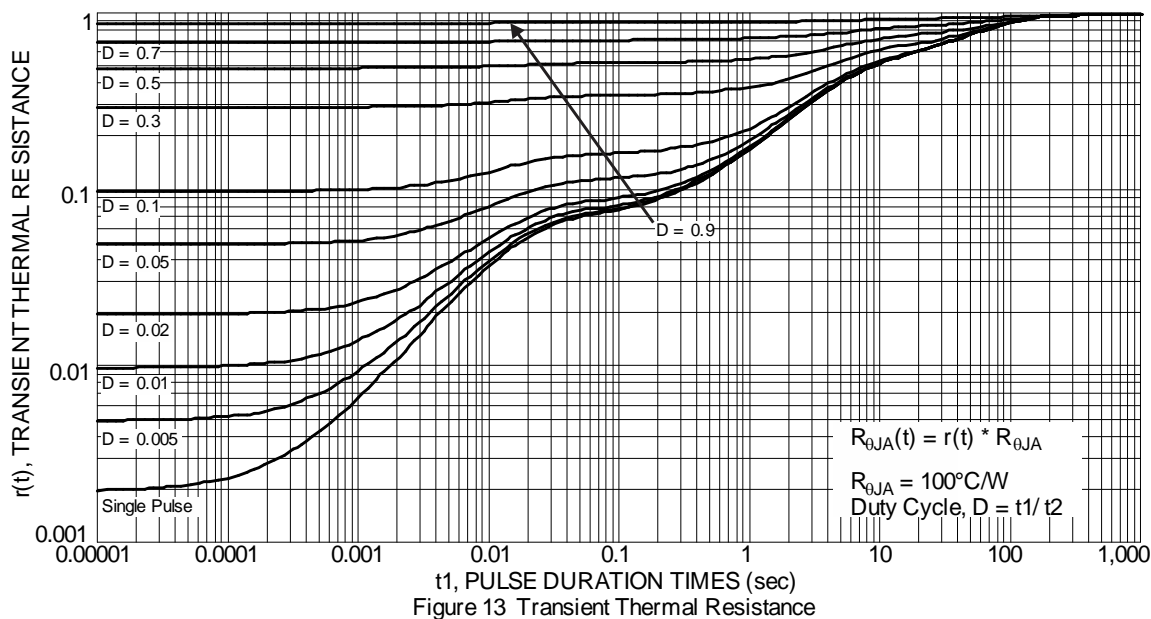
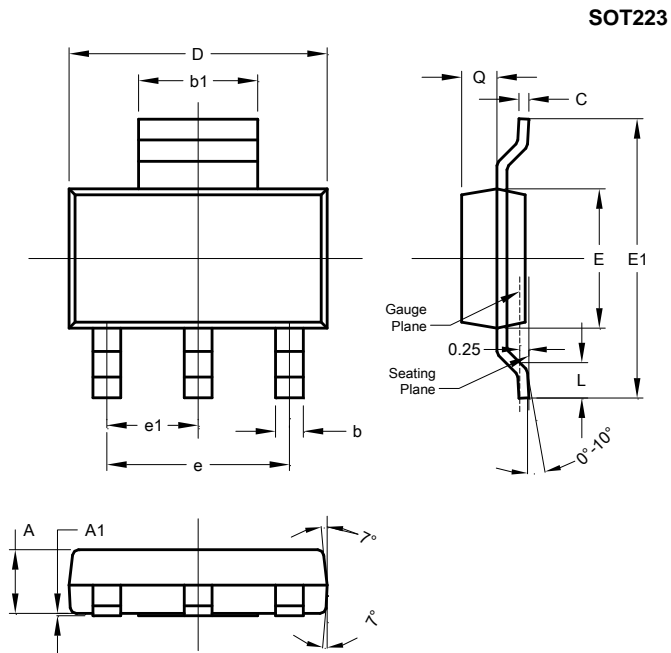


Figure 12 SOA, Safe Operation Area

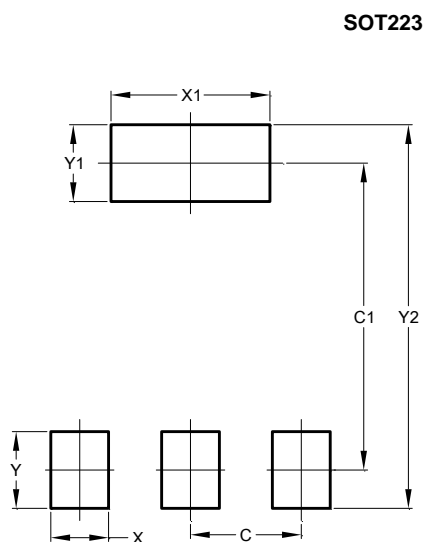


Package Outline Dimensions



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00